

# **2022 20th Non-Volatile Memory Technology Symposium (NVMTS 2022)**

**Stanford, California, USA  
7-9 December 2022**



**IEEE Catalog Number: CFP22NVM-POD  
ISBN: 979-8-3503-0110-6**

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IEEE Catalog Number:	CFP22NVM-POD
ISBN (Print-On-Demand):	979-8-3503-0110-6
ISBN (Online):	979-8-3503-0109-0
ISSN:	2689-1395

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December 7 - 9, 2022, Stanford University, California, United States of America

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